

based designs dissipated around 10x less power than its CNT-FET and finFET counterparts, which proves Graphene based devices to be a superlative choice to combat power dissipation, with increased scaling. The different designs provide a varied performance over access times measurement. GNR-FET based design shows the least write delay amongst the three designs, whereas CNT-FET based design performs marginally better while writing onto the bit line. Both GNR-FET and SWCNT-FET based designs outperform the silicon FET based design while still providing a future for further scaling.

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